

PROCESS FOR FORMING FEATURES OF 50 NM OR LESS HALF-PITCH WITH CHEMICALLY AMPLIFIED RESIST IMAGING

Abstract

Lithographic imaging of 50 nm (or less) half-pitch features in chemically amplified resists (commonly used in the manufacture of integrated circuits) is enabled by the use of reduced temperature post-exposure processing and low activation energy chemically amplified resists. The post-exposure processing preferably involves ambient to moderately elevated temperature and the presence of a deprotection reaction-dependent co-reactant (e.g., water).